■PHOTO TRANSISTOR

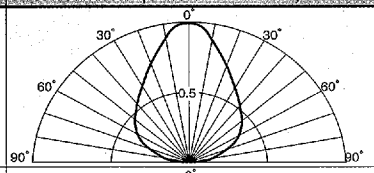
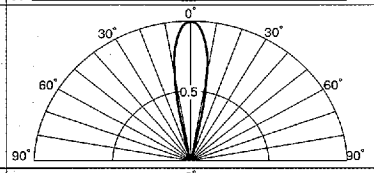
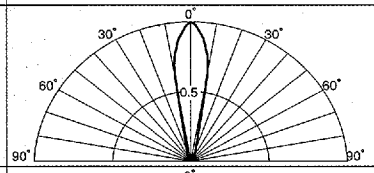
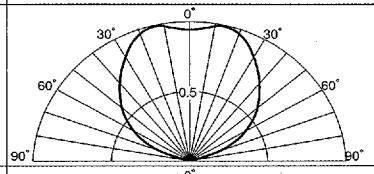
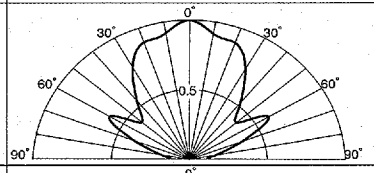
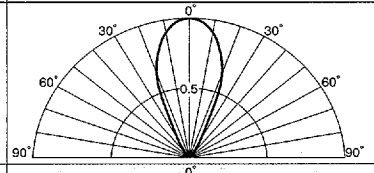
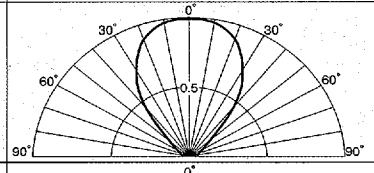
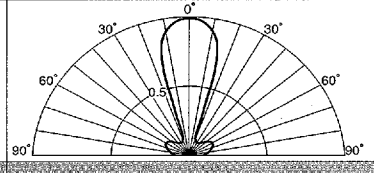
▼CHARACTERISTICS BY MATERIAL

Ta=25℃

Type No.		Absolute Maximum						Electro-Optical Characteristics						
		Collector Dissipation	Emitter-Collector Breakdown Voltage	Collector-Emitter Breakdown Voltage	Collector Current	Operating Temp.	Storage Temp.	Dark Current I_{CEO}		Dark Current T_r T_f				Peak Sensitive Wavelength
	Type	P_C	V_{ECO}	V_{CEO}	I_C	Topr	Tstg	MAX.	V_{CEP}	TYP.	V_{CE}	I_C	R_L	λp TYP.
PS	TO-18	150	30	5	50	−30~+125	−30~+150	0.2	10	5	10	2	100	880
	502	60			20	−30~+85	−30~+100							
		100			30									
Units		mW	V	V	mA	℃	℃	μA	V	μsec	V	mA	Ω	nm

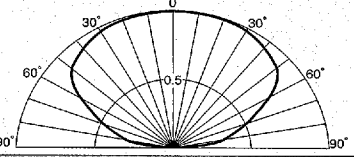
▼CHARACTERISTICS BY SHAPE

Ta=25℃

Shape	Type No.	Features	Peak Sensitive Wavelength λp TYP.	Photo Current I_C MIN.	Photo Current I_C TYP.	I_C V_{CE}	I_C Ee	Spatial Distribution (The typical distribution example of each shape is shown below)	fig.
	PS2022	TO-18 can type, flat lens	880	0.1	2.5	5	1		20
	PS3022	φ5 molded epoxy type, high-directivity lens	880	1.5	7	5	1		21
	PS3322	φ3 molded epoxy type, high-directivity lens	880	1.2	3.6	5	1		22
	PS3072	φ3 molded epoxy type	880	0.2	0.7	5	1		23
	PS4032	φ3 molded epoxy type, flat lens	880	1.5	5	5	10		24
	PS5022	φ1.7 axial-lead type	880	0.4	2	5	1		25
	PS5042	φ3.6 side-view type	880	0.4	1.4	5	1		26
	PS5052	side-view type high-directivity	880	0.3	1.4	5	1		27
Units			nm	mA		V	mW/cm^2		

▼CHARACTERISTICS BY SHAPE

Ta=25℃

Shape	Type No.	Features	Peak Sensitive Wavelength λp TYP.	Photo Current Ic MIN.	Photo Current Ic TYP.	Ic VCE	Ic Ee	Spatial Distribution (The typical distribution example of each shape is shown below)	fig.
	PS1101W	Chip type	880	0.7	3.5	5	5		28
Units:			nm	mA		V	mW/cm²		

▼PACKAGE DIMENSIONS Unit : mm

fig. 20

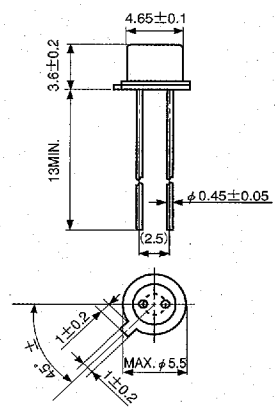


fig. 21

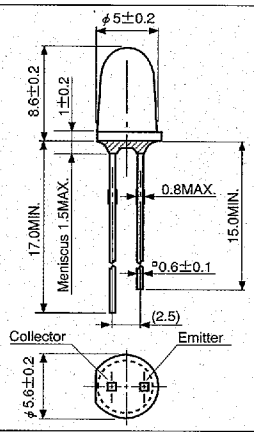


fig. 22

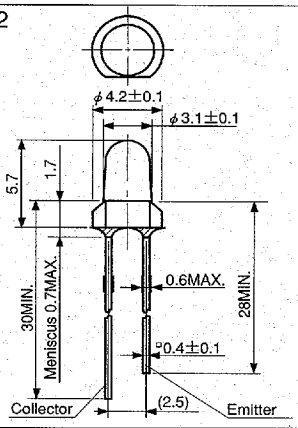


fig. 23

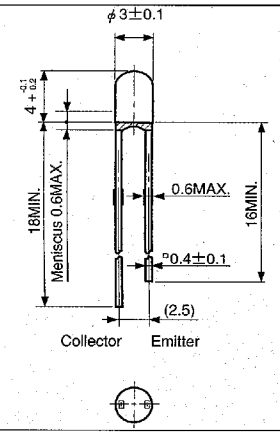


fig. 24

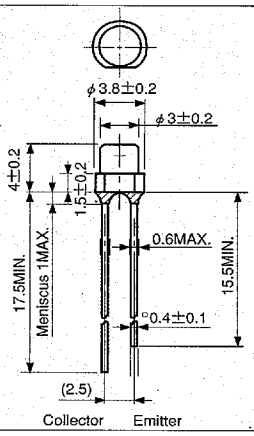


fig. 25

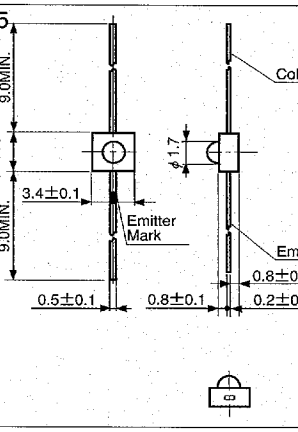


fig. 26

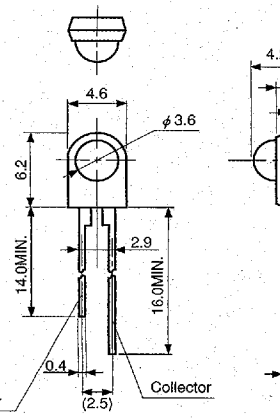


fig. 27

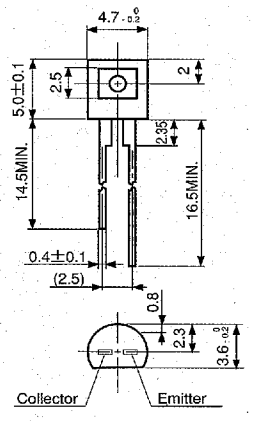


fig. 28